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Understanding Surface Contamination Effects in Mid-T Baked Cavities

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TTC WG high-Q/high-G remote meeting



**U.S. DEPARTMENT
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Introduction & Motivation

- Mid-T baking of Nb cavities is usually carried out at 300–350 °C to enhance their Q-values.
- Mid-T baking in this temperature range can lead to the formation of surface contaminants, primarily niobium carbides. Contamination level depends on furnace cleanliness/residual gases, which vary between furnaces and across facilities.
- **The motivation to perform this study is to:**
 - Determine the effect of the surface contaminants formed during mid-T baking on cavity performance
 - Develop a method to improve cavity performance if the performance is adversely affected by these contaminants



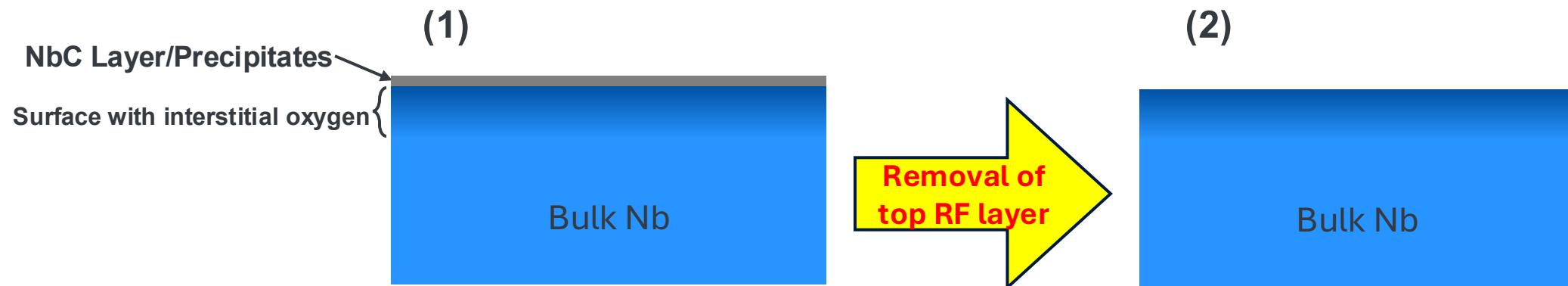
Strategy to determine contaminants effect

To understand the effect of carbides, we must compare performance of the same cavity in two scenarios:

(1) with carbides/contaminants present on the cavity surface

(2) without carbides/contaminants on the cavity surface

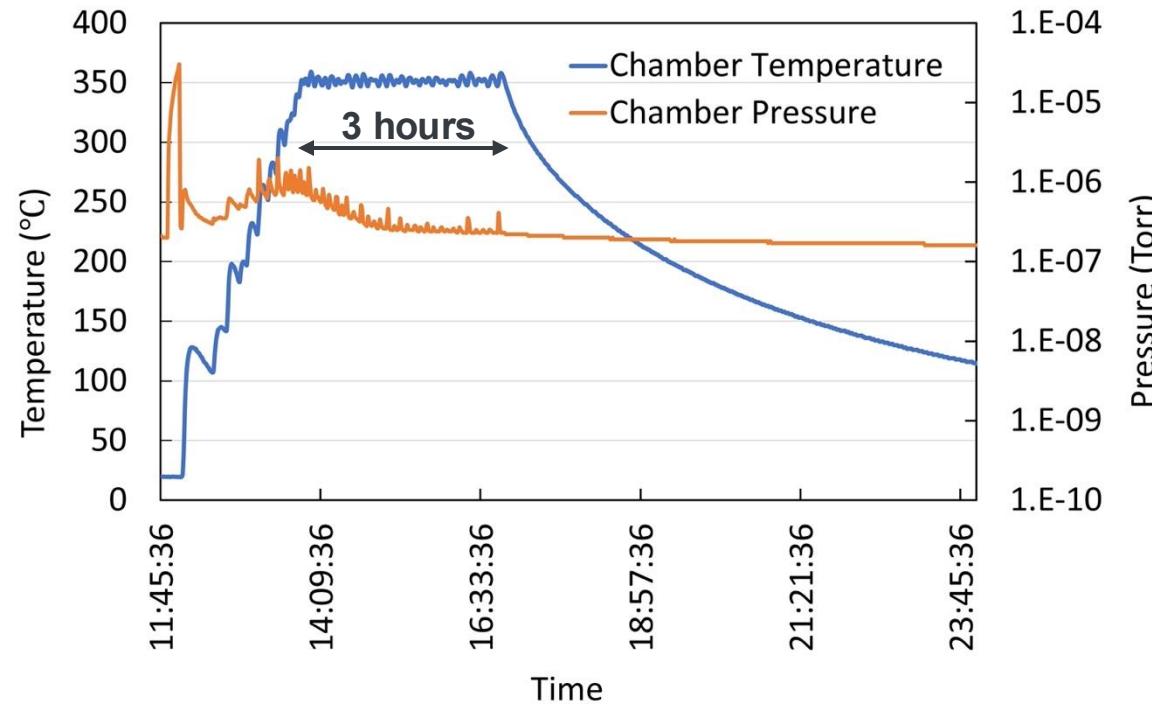
while keeping the oxygen concentration in the RF layer the same in both cases.



Mid-T baking of cavities and samples

- High-gradient cavities were selected for the mid-T baking study.
- Cavities:
 - **1.3 GHz single-cell**
 - **650 MHz single-cell**

Cavities ready to enter furnace



- Both cavities were placed in the furnace and mid-T baked together at **350 °C for 3 hours**.
- Witness samples set in an Nb box were also installed in the furnace.



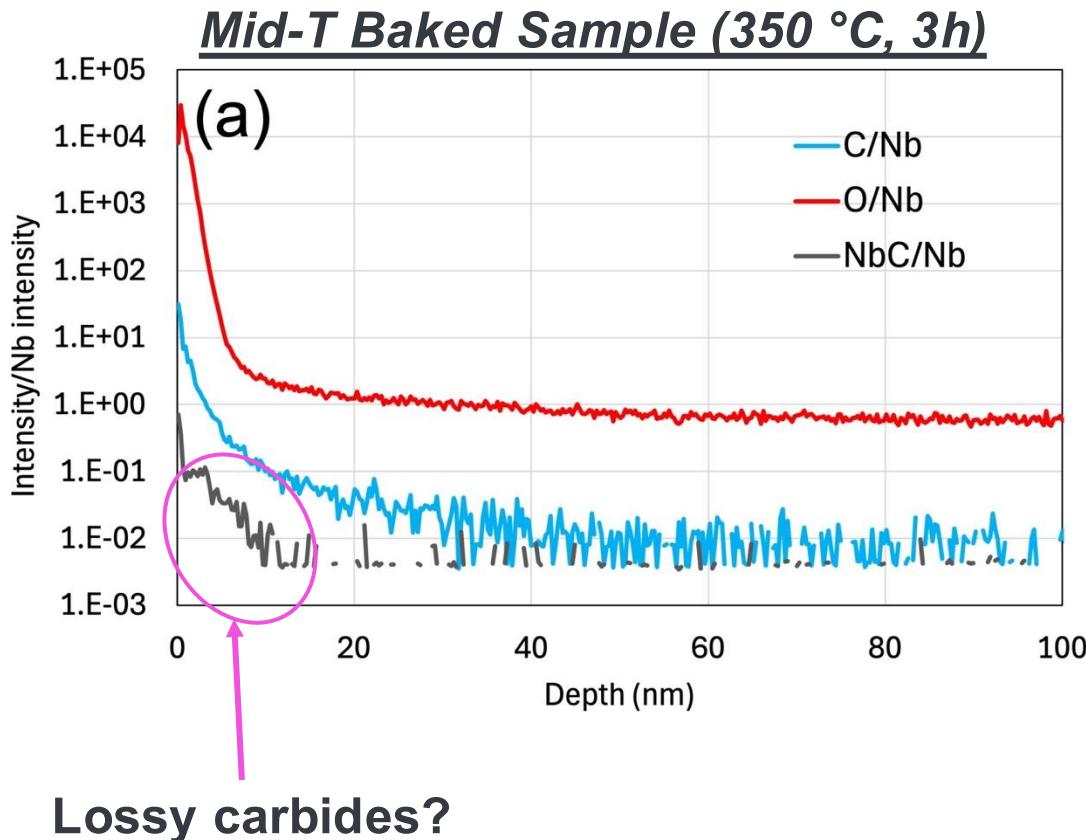
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Sample results



SIMS analysis of mid-T baked sample

- Mid-T baked samples were analyzed with secondary ion mass spectrometry (SIMS) to evaluate surface contaminants.



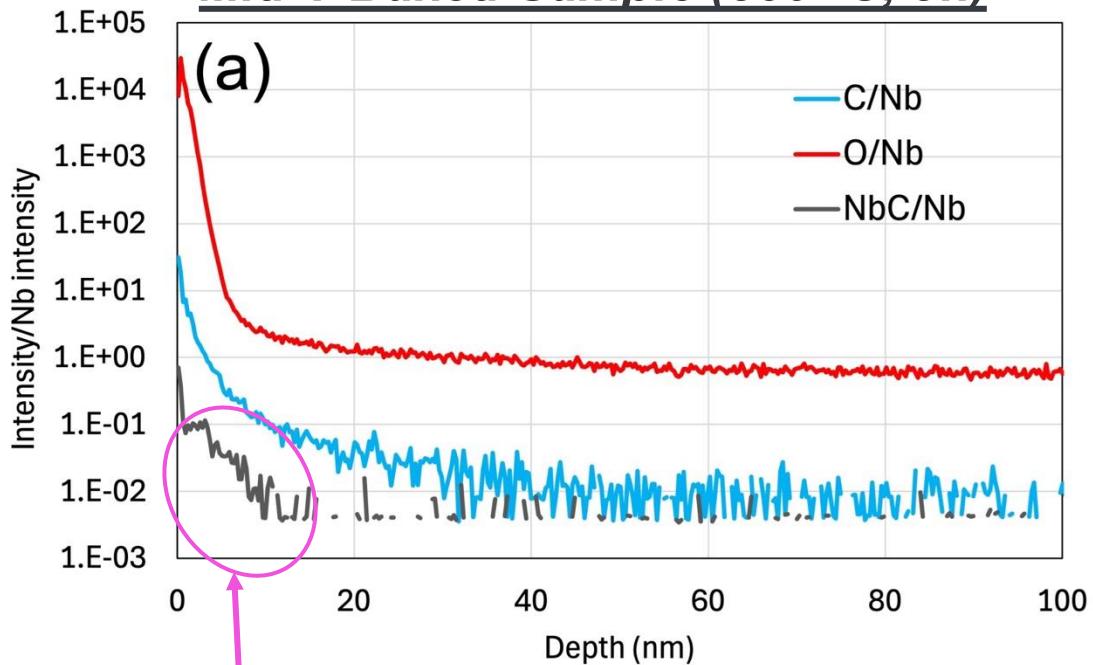
- The SIMS data showed an elevated NbC intensity within the top tens of nanometers of the surface.



SIMS analysis after ultralight EP

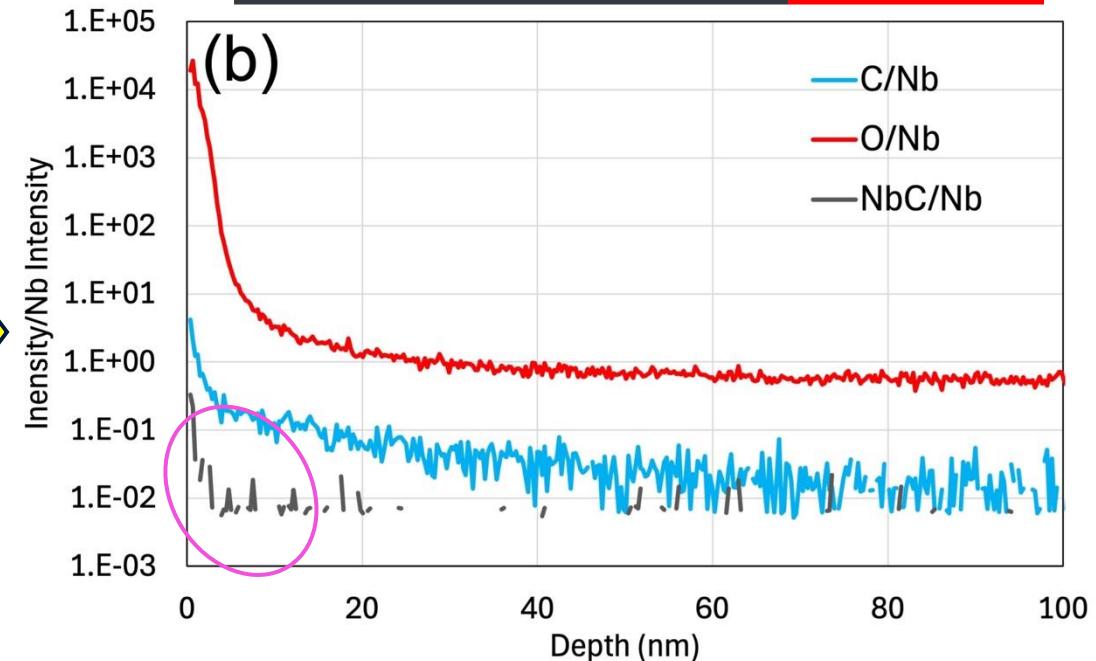
- The spectra were compared with another mid-T baked sample that received **ultralight EP for 120 nm removal**.

Mid-T Baked Sample (350 °C, 3h)



Ultralight EP

Mid-T Baked Sample + 120 nm EP



Lossy carbides?

- NbC intensity was close to the background for the sample subjected to 120 nm removal after mid-T baking.
- Such a difference was observed between mid-T baked and EP-only samples.



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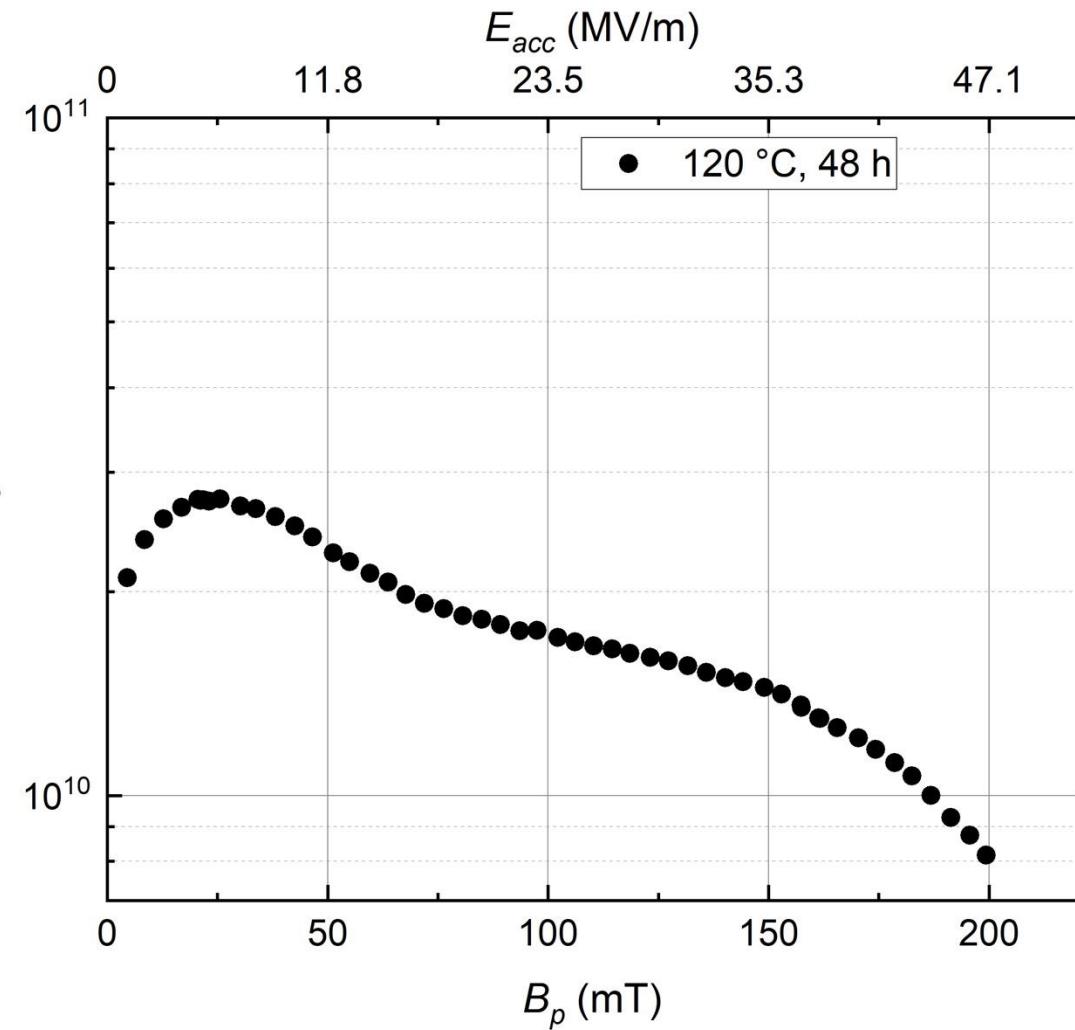
Cavity results

Cavity performance (baseline)

1.3 GHz single-cell cavity

- EP + 120 °C, 48 hrs (baseline)

Cavity reached a high gradient of 47.1 MV/m (200 mT)



Cavity performance (mid-T bake)

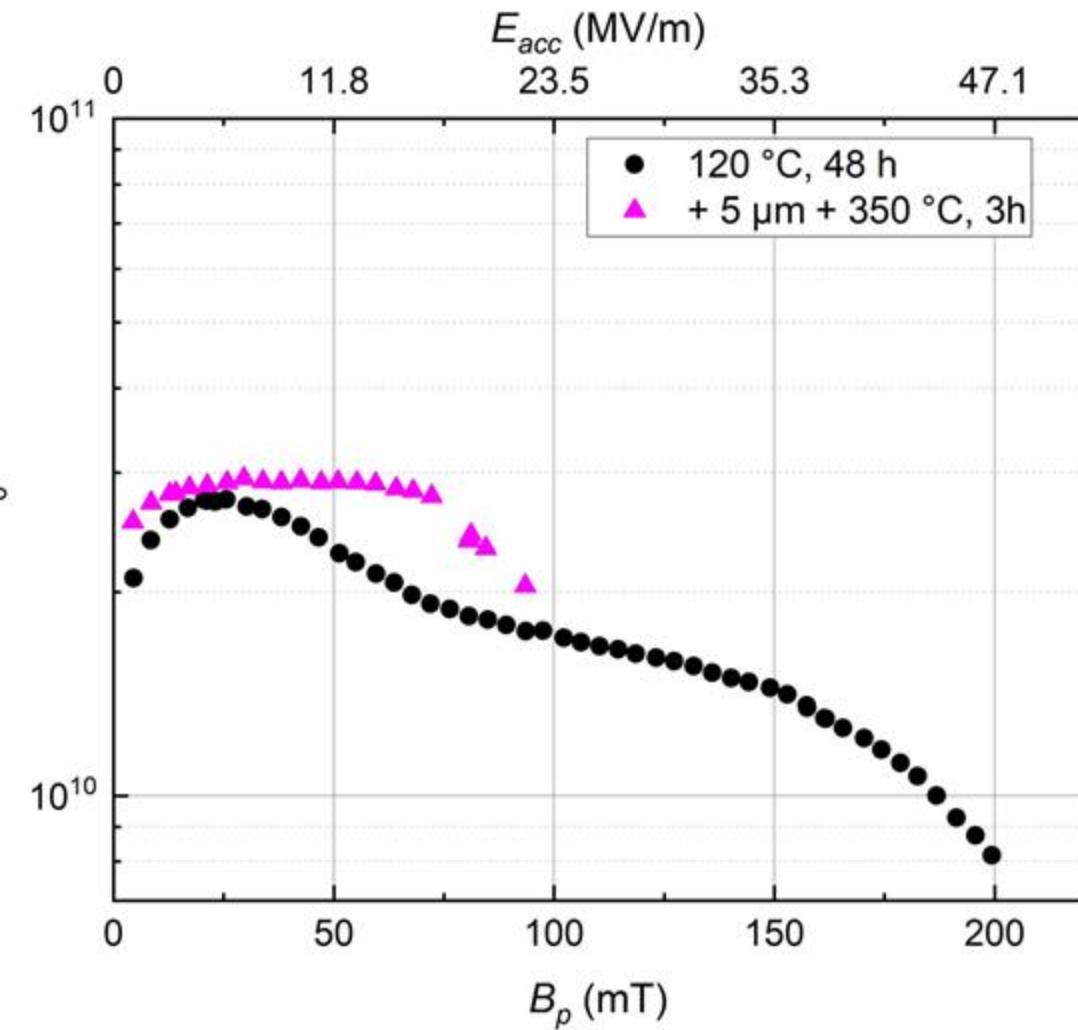
1.3 GHz single-cell cavity

- EP + 120 °C, 48 hrs (baseline)

Cavity reached high gradient of 47.1 MV/m (200 mT)

- Mid-T baking @ 350 °C, 3 hrs

Q value improved, but without a pronounced anti-*Q* slope. Quench field reduced to 22 MV/m.

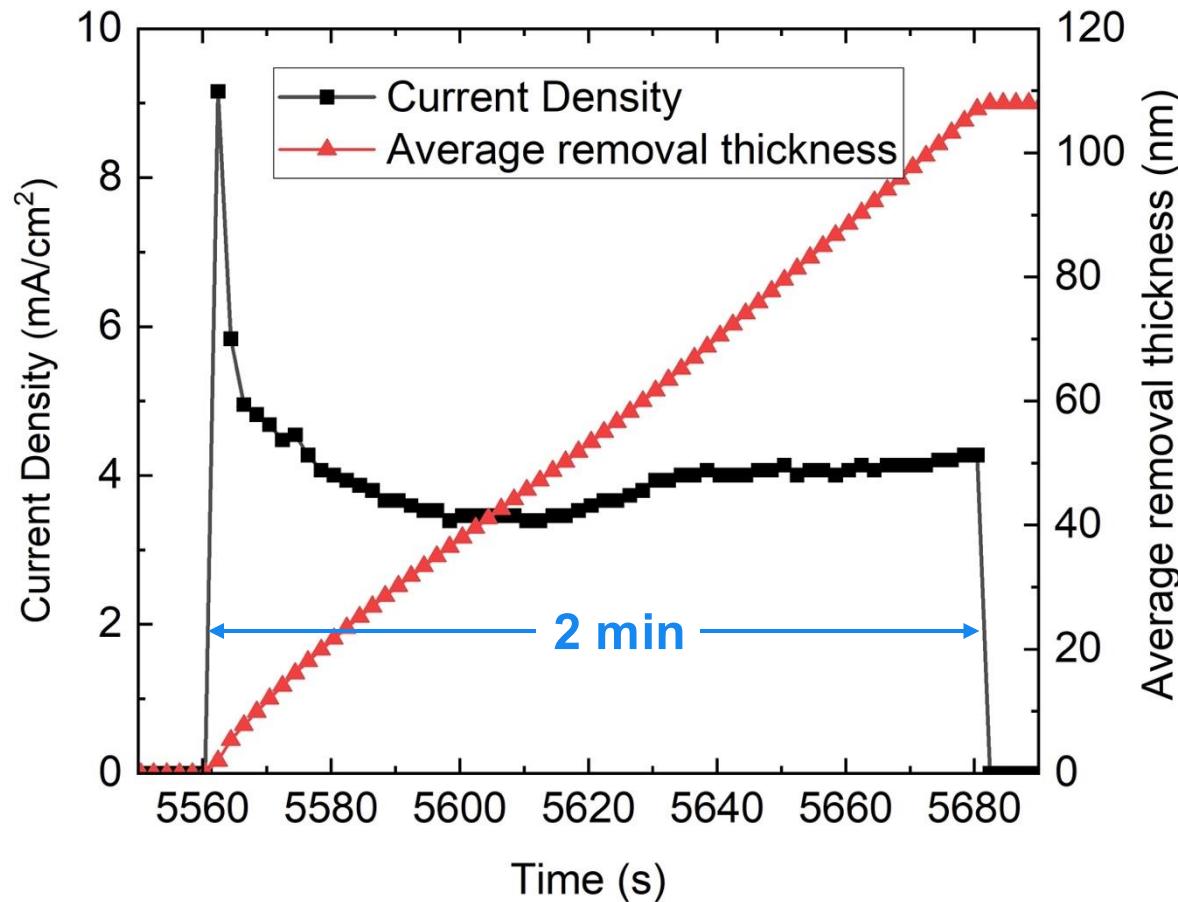




Ultralight EP of mid-T baked cavity

1.3 GHz single-cell cavity

- Ultralight EP for target removal of 100 nm was applied to the cavity.
- The cavity surface temperature during EP was maintained below 6 °C.
- EP was accomplished in 2 minutes.
- Average EP removal thickness was **108 nm**.
- EP was well controlled for circumferentially uniform removal.





Cavity performance (mid-T + ultralight EP)

1.3 GHz single-cell cavity

- EP + 120 °C, 48 hrs (baseline)

Cavity reached a high gradient of 47.1 MV/m (200 mT)

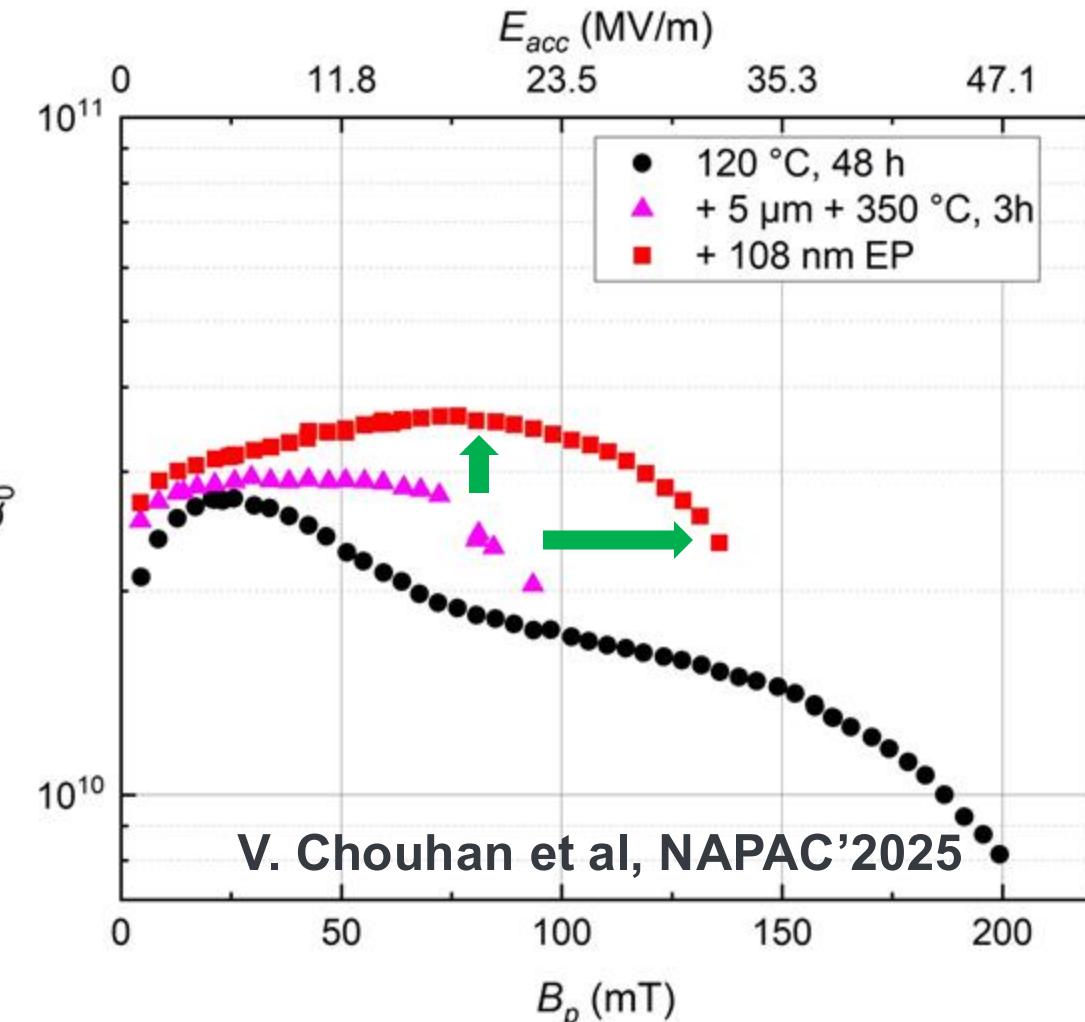
- Mid-T baking @ 350 °C, 3 hrs

Q value improved, but without a pronounced anti-Q slope. Quench field reduced to 22 MV/m.

- Ultralight EP for 108 nm

Q-value improved with an apparent anti-Q slope.

Quench field also improved to 32 MV/m.



- The result confirmed that carbide precipitates degraded the cavity performance.
- Ultralight EP removal improved both gradient and Q value, and it also delayed the onset field for Q-slope.

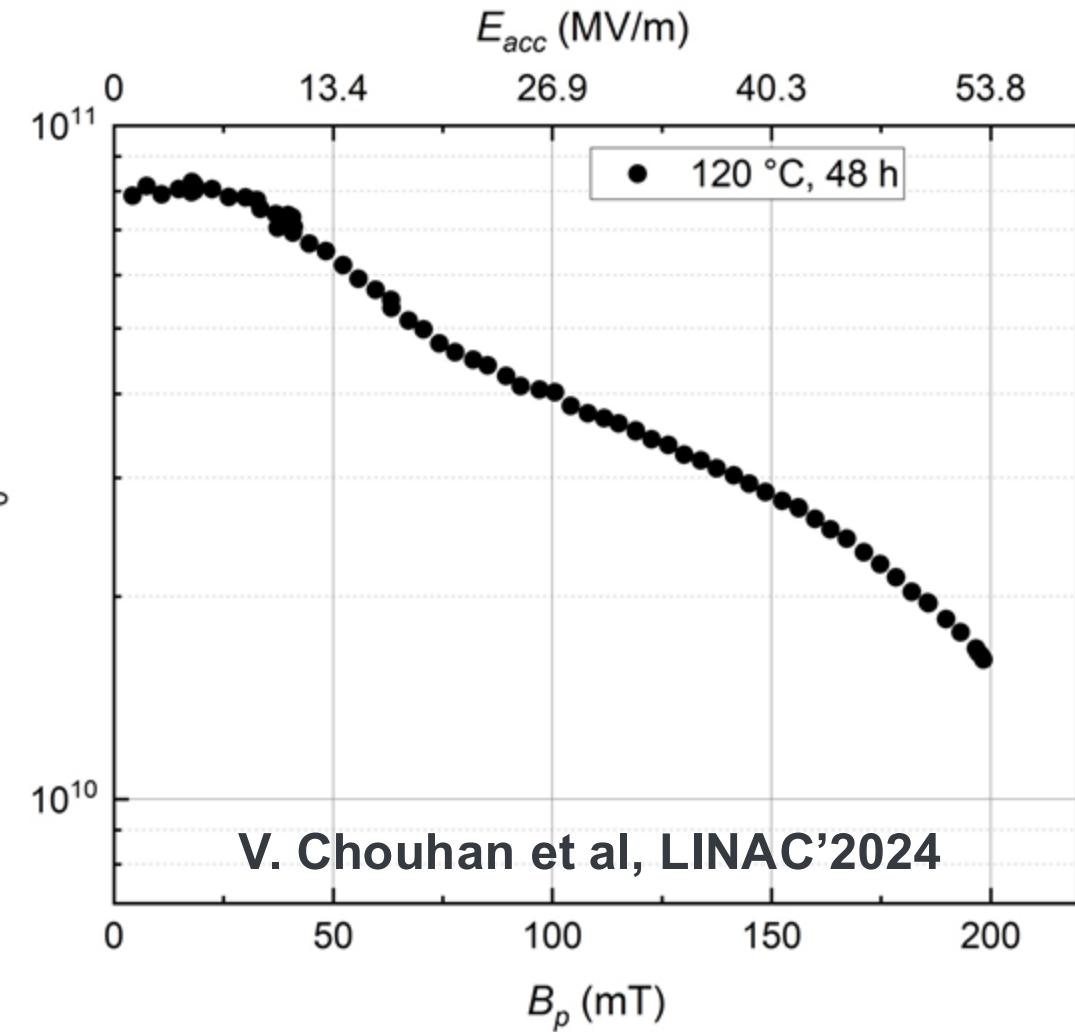


Cavity performance (baseline)

650 MHz single-cell cavity

- EP + 120 °C, 48 hrs (baseline)

Cavity reached a high gradient of 53.3 MV/m (~198 mT)



Cavity performance (mid-T bake)

650 MHz single-cell cavity

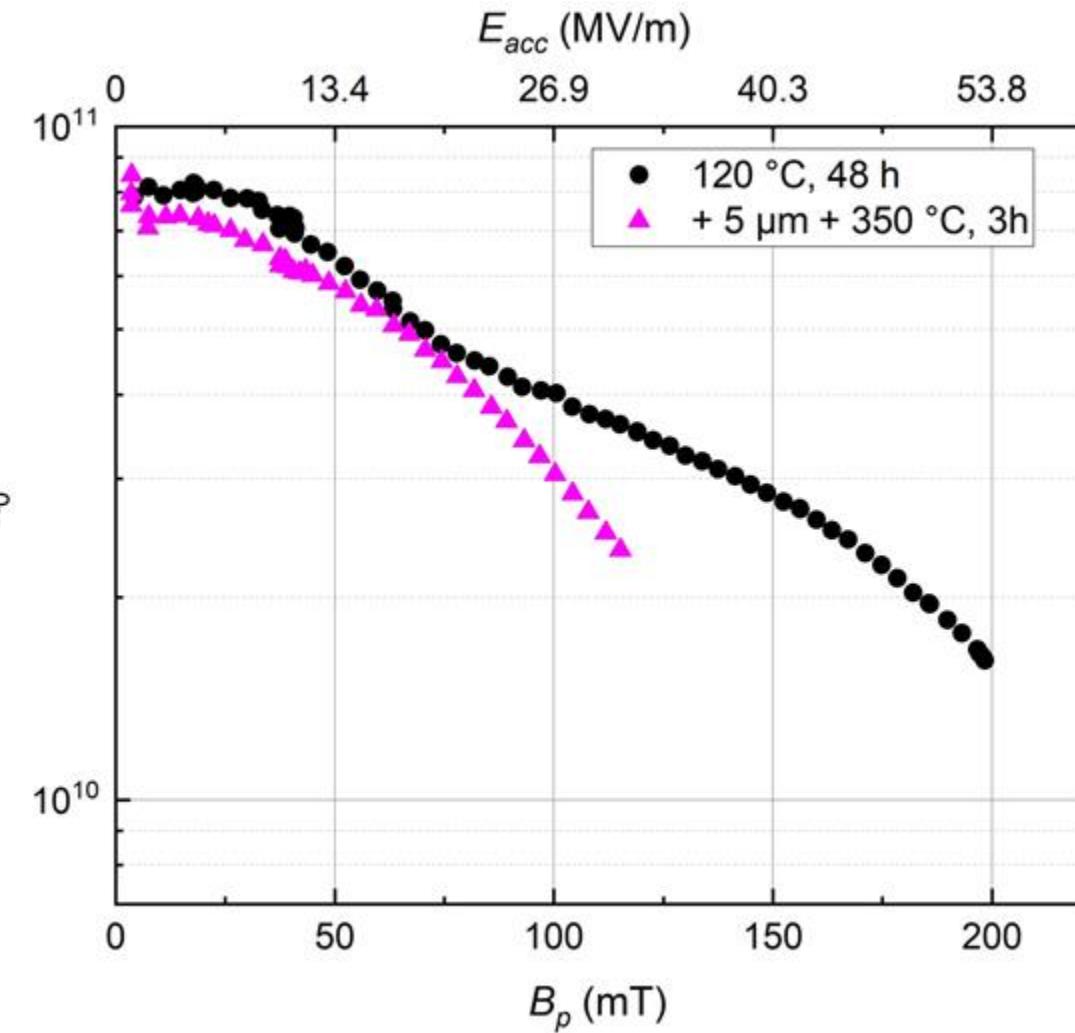
- EP + 120 °C, 48 hrs (baseline)

Cavity reached a high gradient of 53.3 MV/m (~198 mT)

- Mid-T baking @ 350 °C, 3 hrs

Q value was found even lower than that in the baseline.

Quench field reduced to 33.3 MV/m.





Cavity performance (mid-T + ultralight EP)

650 MHz single-cell cavity

- EP + 120 °C, 48 hrs (baseline)

Cavity reached a high gradient of 53.3 MV/m (~198 mT)

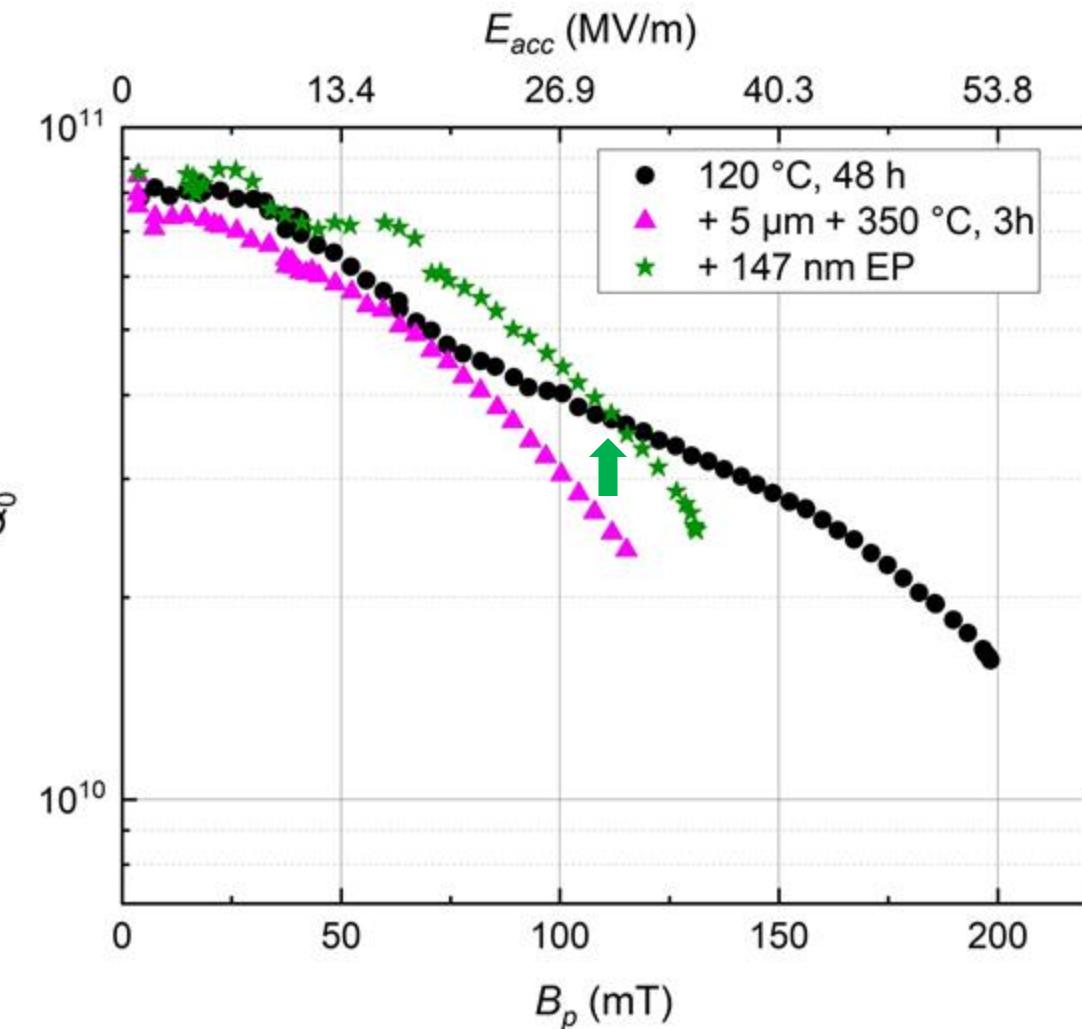
- Mid-T baking @ 350 °C, 3 hrs

Q value was found even lower than that in the baseline.

Quench field reduced to 33.3 MV/m.

- Ultralight EP step-1 for 147 nm

Q-value improved after ultralight EP. Quench field improved marginally.





Cavity performance (mid-T + ultralight EP)

650 MHz single-cell cavity

- EP + 120 °C, 48 hrs (baseline)

Cavity reached a high gradient of 53.3 MV/m (~198 mT)

- Mid-T baking @ 350 °C, 3 hrs

Q value was found even lower than that in the baseline.

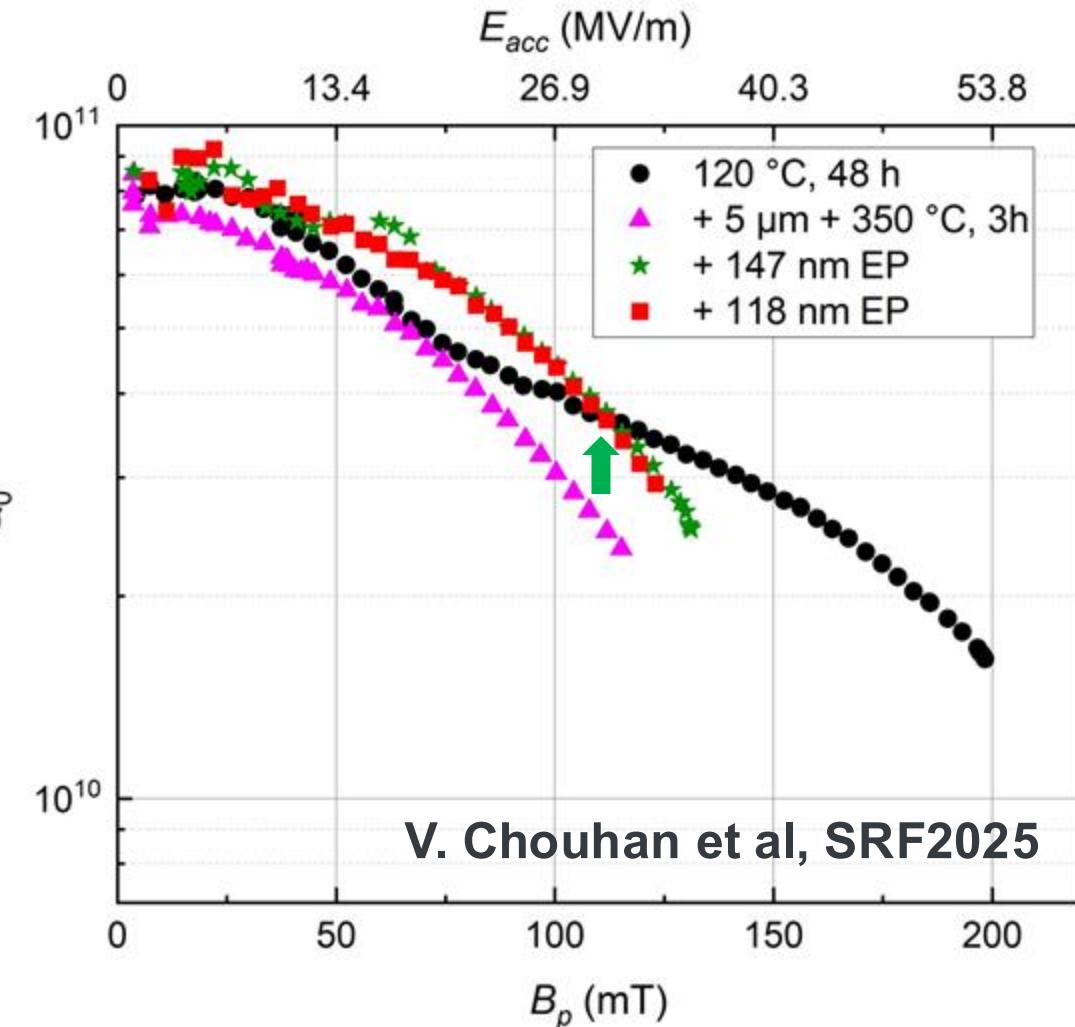
Quench field reduced to 33.3 MV/m.

- Ultralight EP step-1 for 147 nm

Q-value improved after ultralight EP. Quench field improved marginally.

- Ultralight EP step-2 for 118 nm

No further improvement after the second EP step.

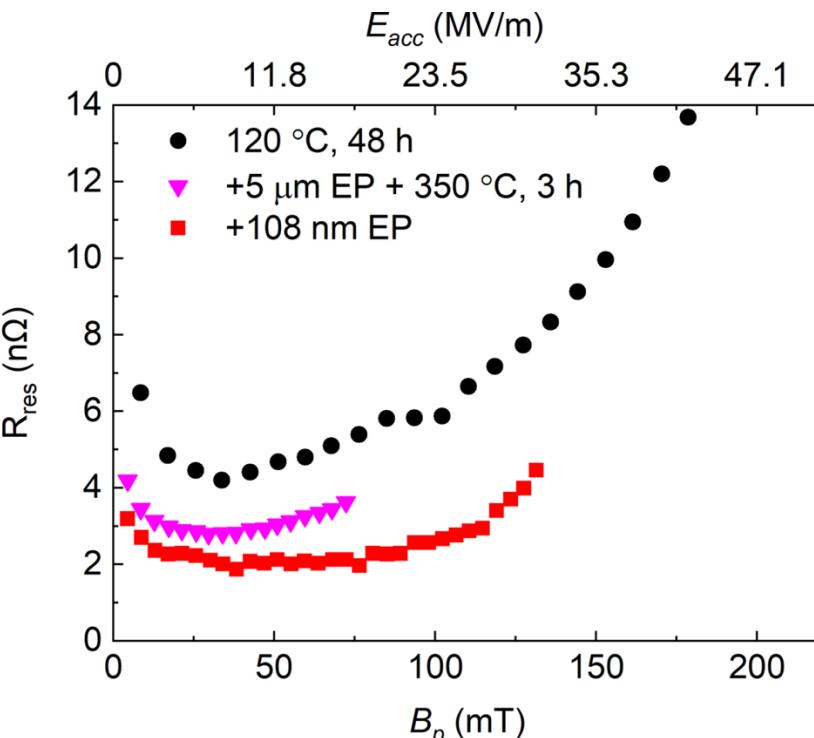
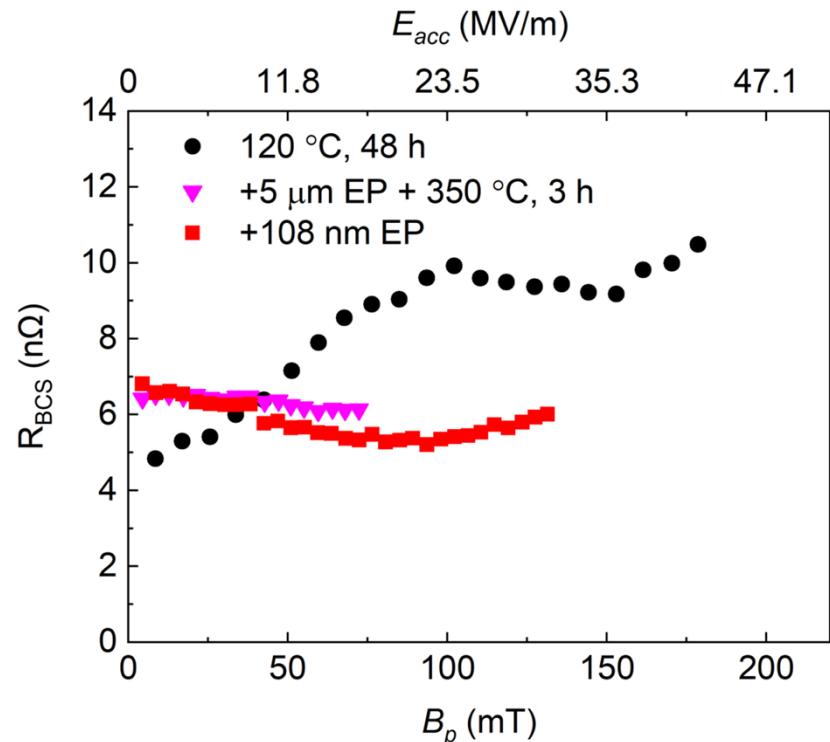
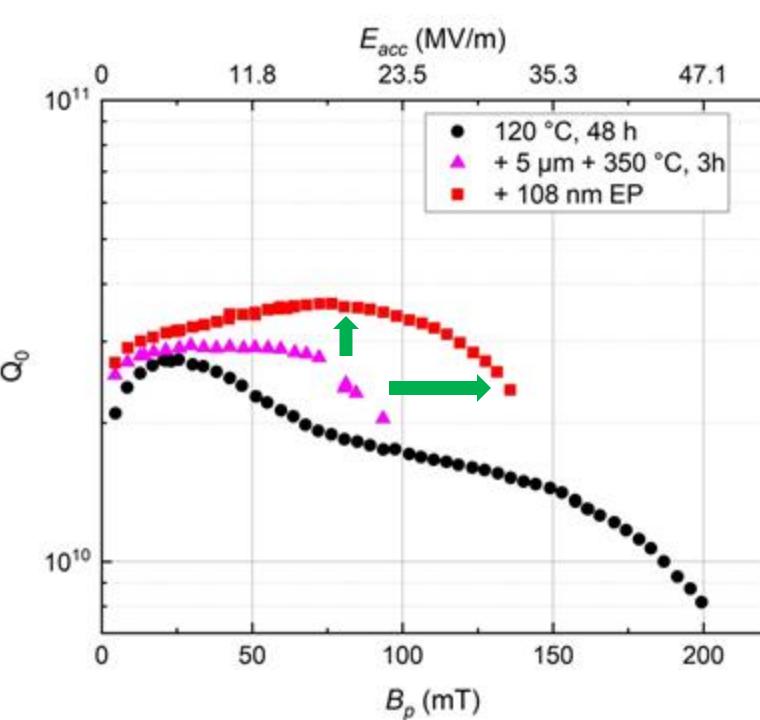


- The ultralight EP effect was demonstrated on the 650 MHz cavity through an improvement in its Q value.
- An additional ultralight EP step did not further improve performance, indicating that the top RF layer with carbide precipitates was responsible for poor performance after mid-T baking.



Cavity surface resistance

1.3 GHz single-cell cavity

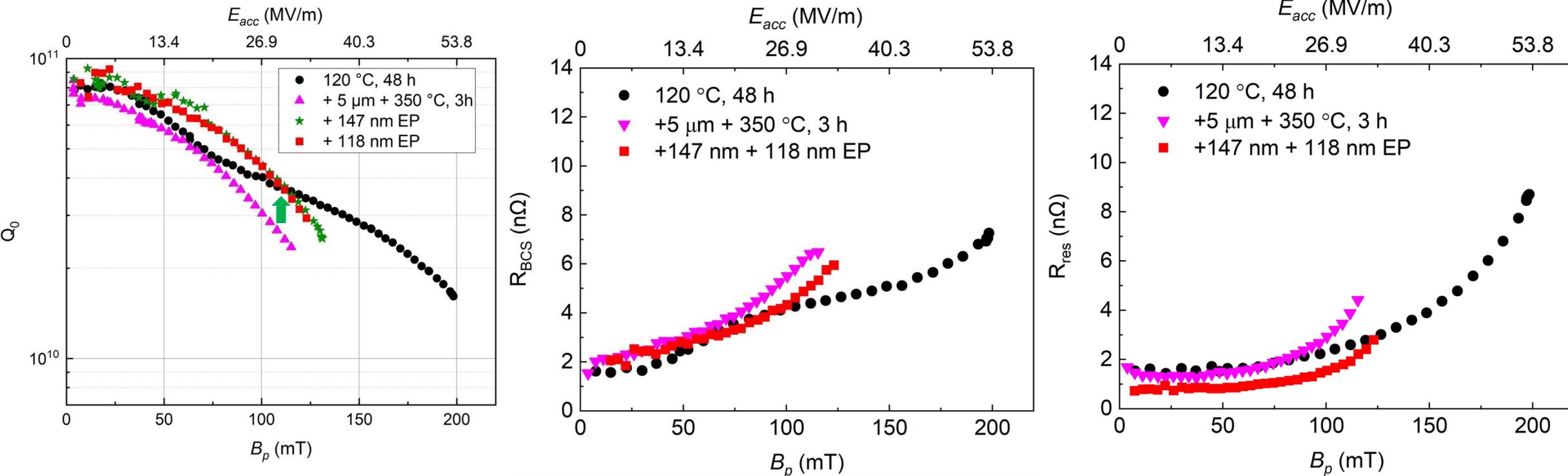


- Carbides primarily affected residual resistance, which contributed to a lower Q value.
- Ultralight EP after mid-T baking significantly reduced residual resistance.
- BCS resistance also decreased, as visible in the higher field range.



Cavity surface resistance

650 MHz single-cell cavity



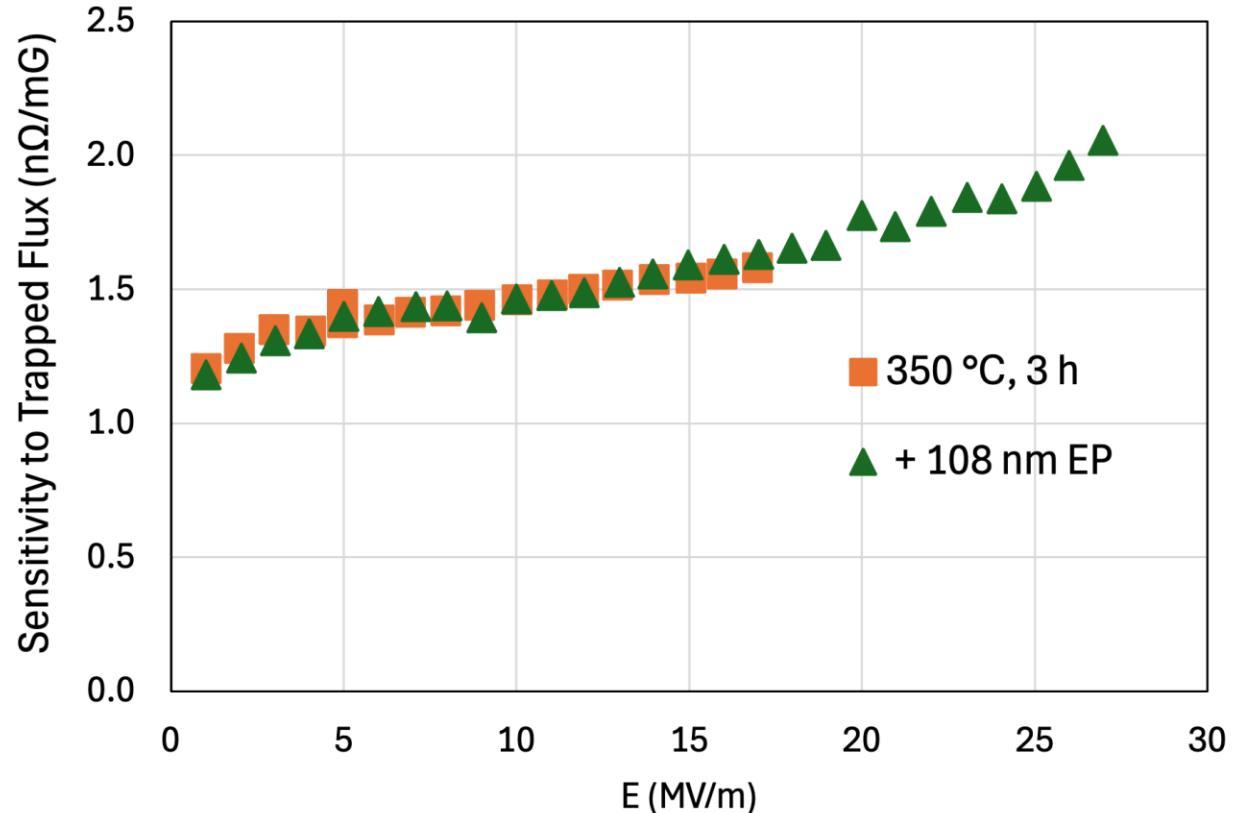
- Ultralight EP effect was similar on the 650 MHz cavity also.
- Residual resistance decreased after ultralight EP, while BCS showed a lower trend for $B_p > 50$ mT.
- The effect of carbides on the surface resistances was higher in a higher field range (> 100 mT), potentially leading to a high field Q-slope.



Sensitivity to Trapped Flux

1.3 GHz Cavity

- The cavity was also tested with a trapped external magnetic field to measure sensitivity to the trapped flux.
- The sensitivities before and after ultralight EP were similar, suggesting that NbC may not change the sensitivity to trapped flux.





Summary

- Mid-T baking study was performed on Nb samples and cavities.
- The results indicated that niobium carbides formed on the surface during mid-T baking conducted at 350 °C for 3 hours, accumulating within the top RF layer.
- An ultralight EP process was developed to selectively remove this top RF layer and was applied to 1.3 GHz and 650 MHz single-cell cavities after mid-T baking.
- Both cavities showed significant performance improvement following ultralight EP, suggesting that carbides/contaminants removal is beneficial.
- Further study is required to get statistics and to evaluate carbide and ultralight EP effects on 300 °C baked cavities.



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